

MOS FIELD EFFECT TRANSISTOR 2SK3482

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3482 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

· Low on-state resistance

 $R_{DS(on)1}$ = 33 m Ω MAX. (Vgs = 10 V, ID = 18 A)

 $R_{DS(on)2} = 39 \text{ m}\Omega \text{ MAX.}$ (Vgs = 4.5 V, ID = 18 A)

- Low Ciss: Ciss = 3600 pF TYP.
- · Built-in gate protection diode
- TO-251/TO-252 package

★ ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3482	TO-251 (MP-3)		
2SK3482-Z	TO-252 (MP-3Z)		

(TO-251)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	100	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	±20	V
Drain Current (DC)	I _{D(DC)}	±36	Α
Drain Current (Pulse) Note1	I _{D(pulse)}	±100	Α
Total Power Dissipation (Tc = 25°C)	Рт	50	W
Total Power Dissipation (T _A = 25°C)	Рт	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	30	Α
Single Avalanche Energy Note2	Eas	90	mJ



TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

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查询ECTRICALZUHARATETERISTICS (TA = 25°C)

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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 100 V, V _{GS} = 0 V			10	μΑ
Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	٧
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 18 A	12	23		S
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = 10 V, I _D = 18 A		27	33	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 18 A		29	39	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		3600		pF
Output Capacitance	Coss	V _{GS} = 0 V		360		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		190		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 50 V, I _D = 18 A		15		ns
Rise Time	tr	V _{GS} = 10 V		10		ns
Turn-off Delay Time	td(off)	$R_G = 0 \Omega$		68		ns
Fall Time	tf			6		ns
Total Gate Charge	Q _G	V _{DD} = 80 V		72		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		10		nC
Gate to Drain Charge	Q _{GD}	I _D = 36 A		19		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 36 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t rr	I _F = 36 A, V _{GS} = 0 V		70		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		180		nC

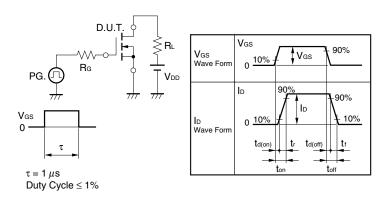
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD}

Starting Tch

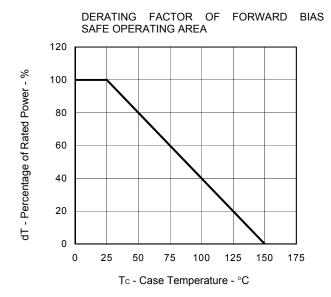
TEST CIRCUIT 2 SWITCHING TIME

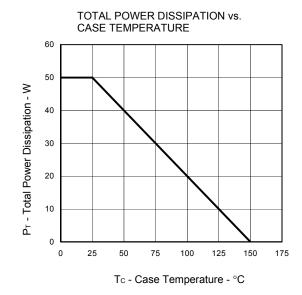


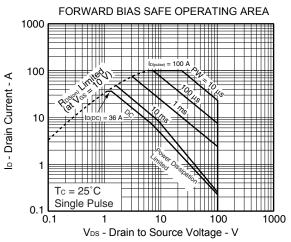
TEST CIRCUIT 3 GATE CHARGE

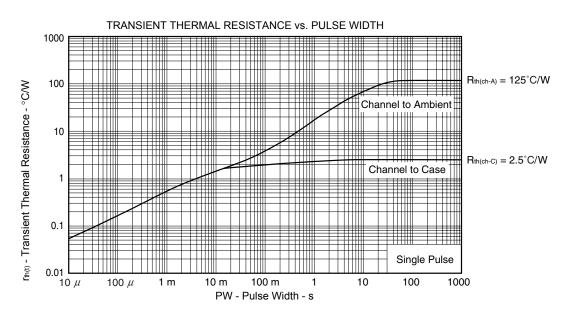


查询PCAL3CHARACTERISTICS (TA = 25°C)



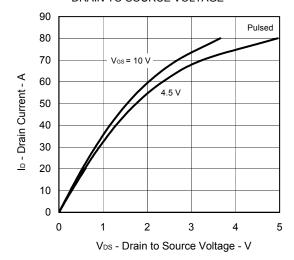




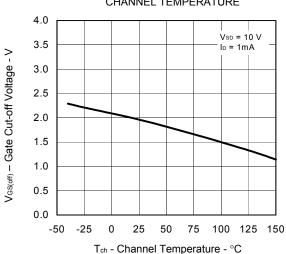


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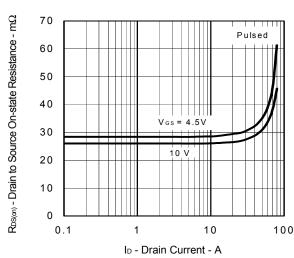
查询"2SK34**9&AN'(地府商**T vs. DRAIN TO SOURCE VOLTAGE



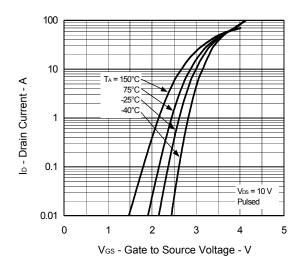
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



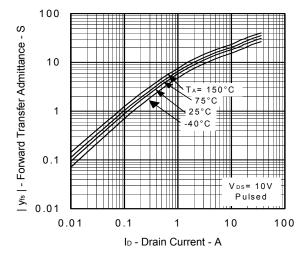
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



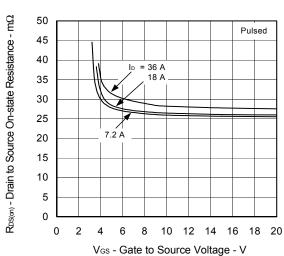
FORWARD TRANSFER CHARACTERISTICS



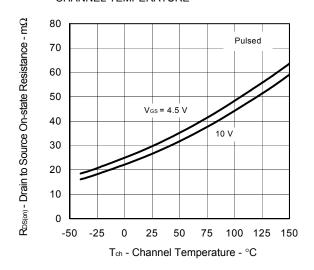
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



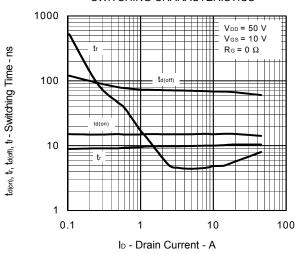
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



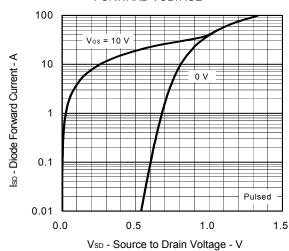
查询"2SK3482-Z"供应商 DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



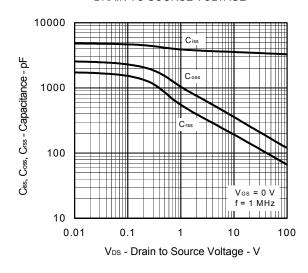
SWITCHING CHARACTERISTICS



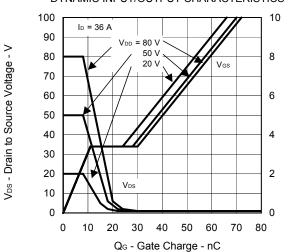
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



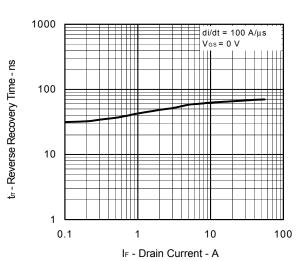
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



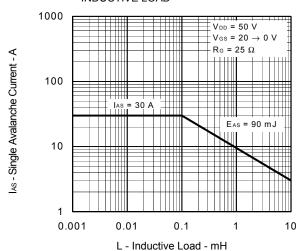
REVERSE RECOVERY TIME vs. DRAIN CURRENT



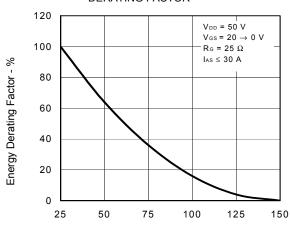
Ves - Gate to Drain Voltage - V

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SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



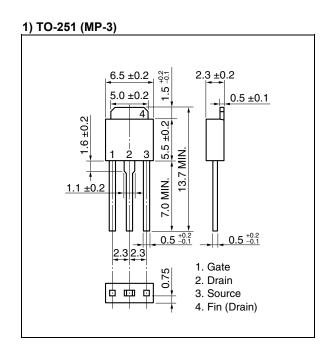
SINGLE AVALANCHE ENERGY DERATING FACTOR

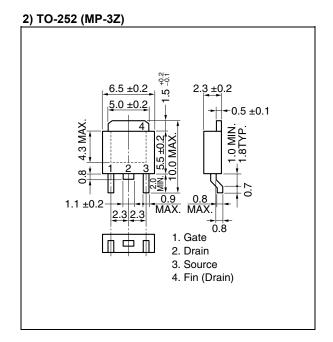


Starting T $_{\text{ch}}$ - Starting Channel Temperature - $^{\circ}\text{C}$

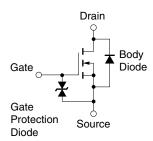


★查询 CRAGE BRAWNS (Unit: mm)





EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Data Sheet D15064EJ2V0DS

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